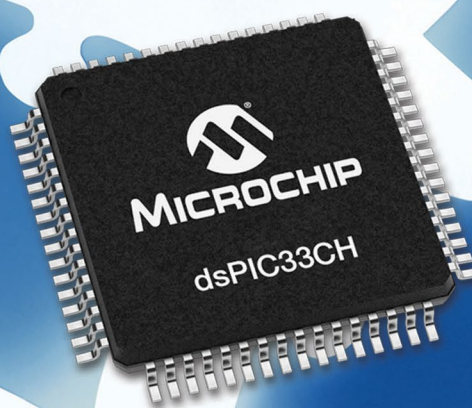


Bodo's Power Systems®

Electronics in Motion and Conversion

August 2018

Dual-Core dsPIC® Digital Signal Controller Enables Separate Code Design and Seamless Integration

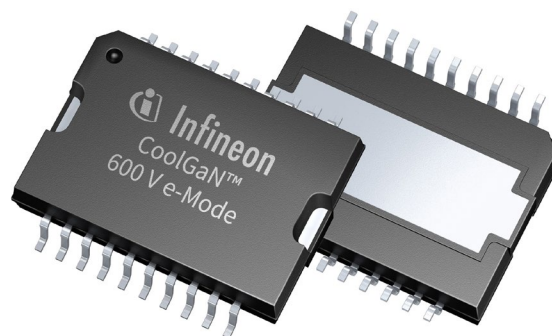


CoolGaN™ Opens up for a New Horizon in Power Management

The key benefits of gallium nitride (GaN) are, amongst others, high power density, best-in-class efficiency and decreased system costs. Infineon Technologies AG is starting volume production for Cool-GaN™ products by the end of 2018, the company announced during PCIM Europe. Engineering samples of the high reliable GaN solution in the market are available now.

"Infineon is the global leader in power solutions and we truly believe that the next big thing in power management is gallium nitride," said Steffen Metzger, Senior Director High Voltage Conversion at Infineon. "Our goal is to be the first choice for customers when it comes to GaN power, and we have all assets in place to live up to this ambition. The market for GaN has been gaining a strong momentum; the advantages of using this technology in certain applications are evident. From operating expense and capital expenditure reduction, through higher power density enabling smaller and lighter designs, to overall system cost reduction, the benefits are compelling."

Infineon's CoolGaN is the one of most reliable and globally qualified GaN solutions in the market. During the quality management process not only the device is tested, but also its behavior in the application.



The performance of CoolGaN is beyond other GaN products in the market. At 100 ppm (parts per million), its predicted lifetime is about 55 years, exceeding the expected lifespan by 40 years. CoolGaN enables for example doubled output power in a given energy storage slot size, freeing up space and realizing higher efficiency at the same time.

www.infineon.com/gan

SiC Diodes for Demanding Automotive Applications

ON Semiconductor (Nasdaq: ON), driving energy efficient innovations, has announced an expansion of its silicon carbide (SiC) Schottky diode portfolio to include devices specifically intended for demanding automotive applications. The new AEC-Q101 automotive grade



SiC diodes deliver the reliability and ruggedness needed by modern automotive applications, along with the numerous performance benefits synonymous with Wide Band Gap (WBG) technologies.

SiC technology provides superior switching performance and higher reliability compared to silicon devices. The diodes have no reverse recovery current, and switching performance is independent of temperature. Excellent thermal performance, increased power density and reduced EMI, as well as decreased system size and cost make SiC a compelling choice for the growing number of high-performance automotive applications.

ON Semiconductor's new SiC diodes are available in popular surface mount and through-hole packages, including TO-247, D2PAK and DPAK. The FF5Hx0120 1200 Volt (V) Gen1 devices, and FF5Hx065 650 V Gen2 devices offer zero reverse recovery, low forward voltage, temperature independent current stability, extremely low leakage current, high surge capacity and a positive temperature coefficient. They deliver improved efficiency while the faster recovery increases switching speeds, thereby reducing the size of magnetic components required.

In order to meet the robustness requirements and perform reliably in the harsh electrical environments of automotive applications, the diodes have been designed to withstand high surge currents. They also include a unique, patented termination structure that improves reliability and enhances stability. Operating temperature range is -55°C to +175°C.

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